

# MOSFET - Single, P-Channel, Small Signal, Gate Zener, SC-75, SC-89

**-20 V, -760 mA**

**NTA4151P, NTE4151P**

## Features

- Low  $R_{DS(on)}$  for Higher Efficiency and Longer Battery Life
- Small Outline Package (1.6 x 1.6 mm)
- SC-75 Standard Gullwing Package
- ESD Protected Gate
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

## Applications

- High Side Load Switch
- DC-DC Conversion
- Small Drive Circuits
- Battery Operated Systems such as Cell Phones, PDAs, Digital Cameras, etc.

## MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		$V_{DS}$	-20	V
Gate-to-Source Voltage		$V_{GS}$	$\pm 6.0$	V
Continuous Drain Current (Note 1)	Steady State	$I_D$	-760	mA
Power Dissipation (Note 1)	Steady State	$P_D$	301 313	mW
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	$I_{DM}$	$\pm 1000$	mA
Operating Junction and Storage Temperature		$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$
Continuous Source Current (Body Diode)		$I_S$	-250	mA
Lead Temperature for Soldering Purposes (1/8 in from case for 10 s)		$T_L$	260	$^\circ\text{C}$
Gate-to-Source ESD Rating – (Human Body Model, Method 3015)		ESD	1800	V

## THERMAL RESISTANCE RATINGS

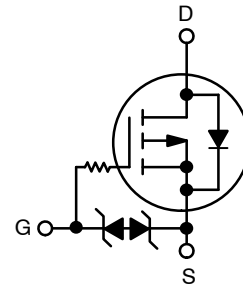
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	415 400	$^\circ\text{C/W}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

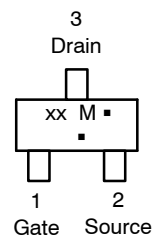
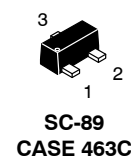
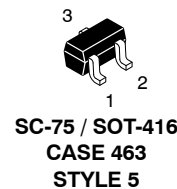
1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	$I_D$ MAX
-20 V	0.26 $\Omega$ @ -4.5 V	-760 mA
	0.35 $\Omega$ @ -2.5 V	
	0.49 $\Omega$ @ -1.8 V	

## P-CHANNEL MOSFET



## MARKING DIAGRAM & PIN ASSIGNMENT



xx = Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\* Date Code orientation may vary depending upon manufacturing location.

## ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# NTA4151P, NTE4151P

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25 °C unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA	-20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = -16 V		-1.0	-100	nA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±4.5 V		±1.0	±10	μA

### ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-0.45		-1.2	V
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -350 mA		0.26	0.36	Ω
		V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -300 mA		0.35	0.45	
		V <sub>GS</sub> = -1.8 V, I <sub>D</sub> = -150 mA		0.49	1.0	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -250 mA		0.4		S

### CHARGES AND CAPACITANCES

Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1.0 MHz, V <sub>DS</sub> = -5.0 V		156		pF
Output Capacitance	C <sub>OSS</sub>			28		
Reverse Transfer Capacitance	C <sub>RSS</sub>			18		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = -4.5 V, V <sub>DD</sub> = -10 V, I <sub>D</sub> = -0.3 A		2.1		nC
Threshold Gate Charge	Q <sub>G(TH)</sub>			0.125		
Gate-to-Source Charge	Q <sub>GS</sub>			0.325		
Gate-to-Drain Charge	Q <sub>GD</sub>			0.5		

### SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t <sub>d(ON)</sub>	V <sub>GS</sub> = -4.5 V, V <sub>DD</sub> = -10 V, I <sub>D</sub> = -200 mA, R <sub>G</sub> = 10 Ω		8.0		ns
Rise Time	t <sub>r</sub>			8.2		
Turn-Off Delay Time	t <sub>d(OFF)</sub>			29		
Fall Time	t <sub>f</sub>			20.4		

### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -250 mA		-0.72	-1.1	V
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Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

3. Switching characteristics are independent of operating junction temperatures.

### ORDERING INFORMATION

Device	Marking	Package	Shipping <sup>†</sup>
NTA4151PT1G	TN	SC-75 (Pb-Free)	3000 / Tape & Reel
NTE4151PT1G	TM	SC-89 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup> For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

TYPICAL ELECTRICAL CHARACTERISTICS

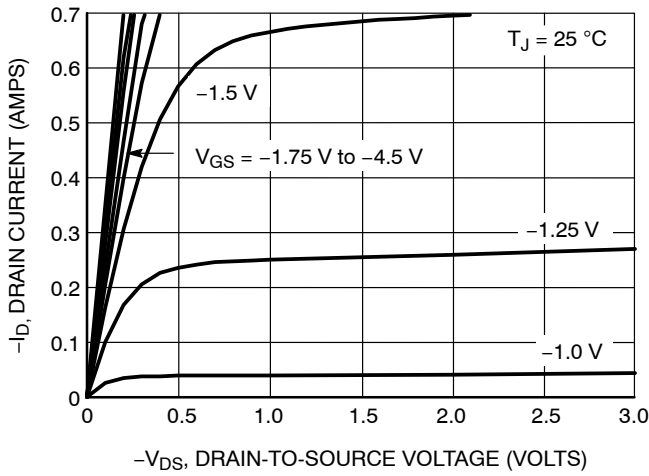


Figure 1. On-Region Characteristics

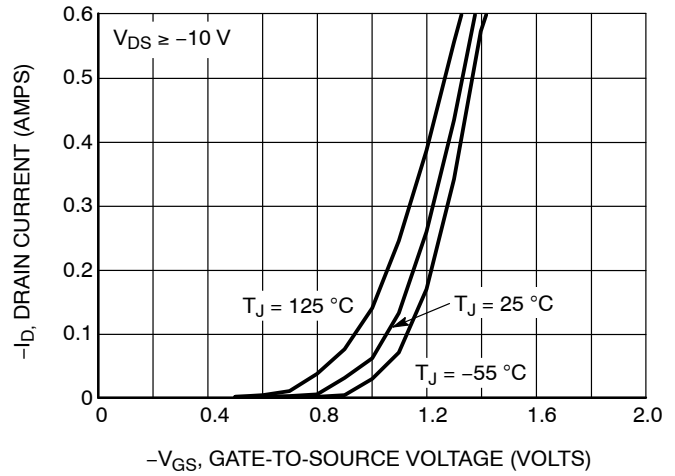


Figure 2. Transfer Characteristics

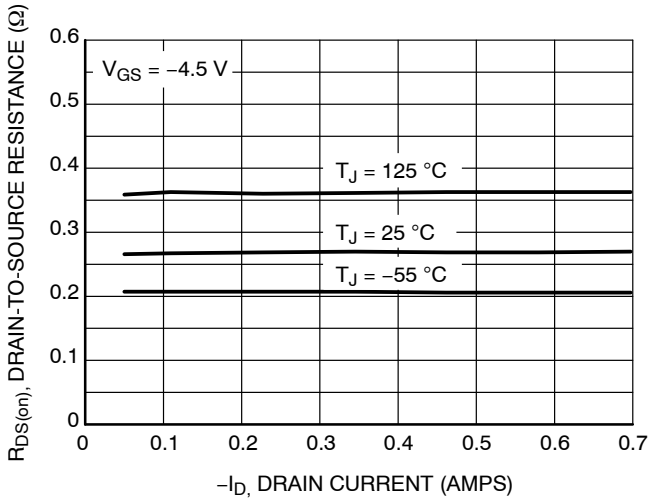


Figure 3. On-Resistance vs. Drain Current and Temperature

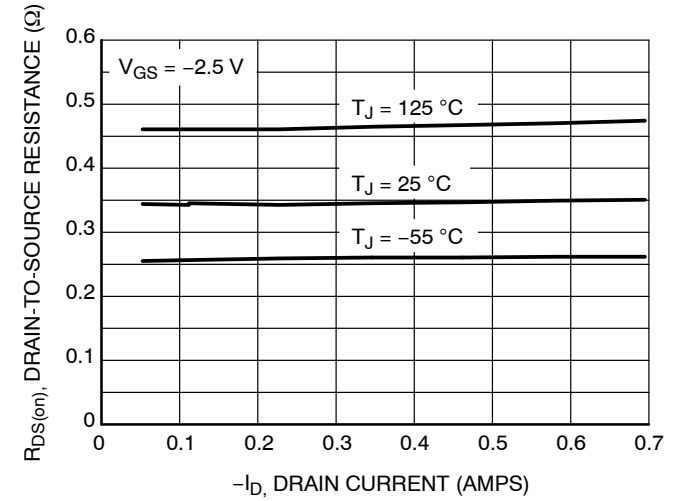


Figure 4. On-Resistance vs. Drain Current and Temperature

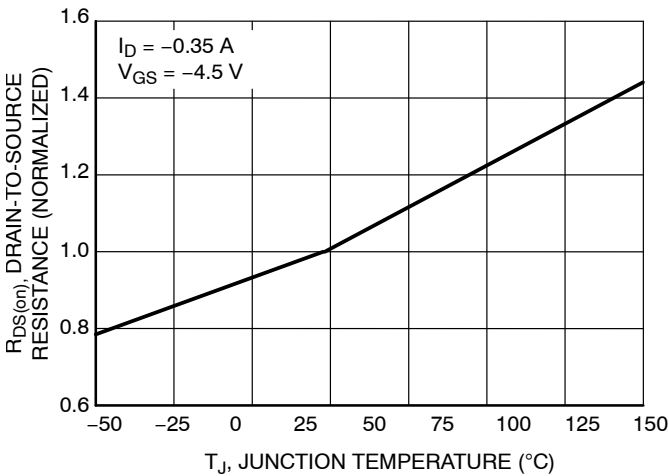


Figure 5. On-Resistance Variation with Temperature

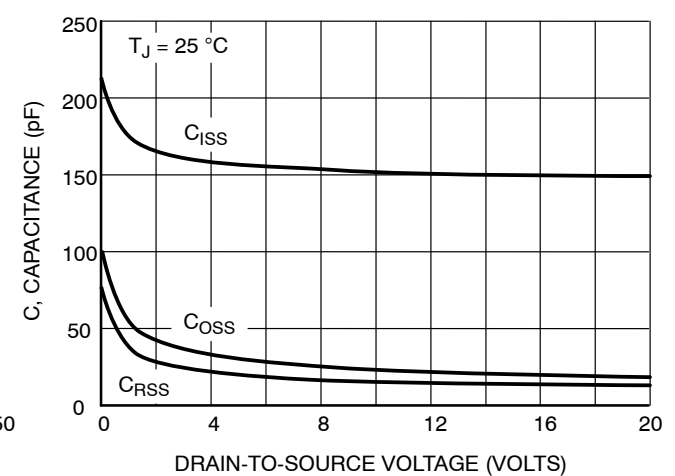
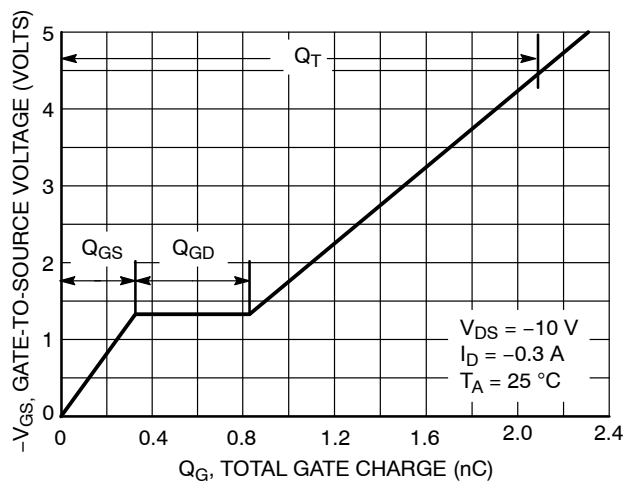


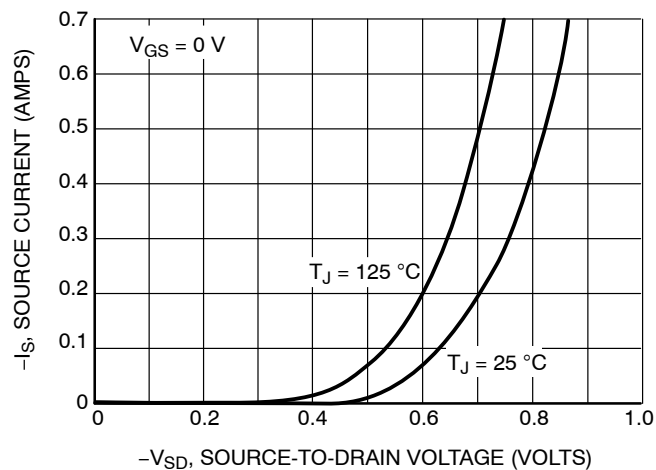
Figure 6. Capacitance Variation

# NTA4151P, NTE4151P

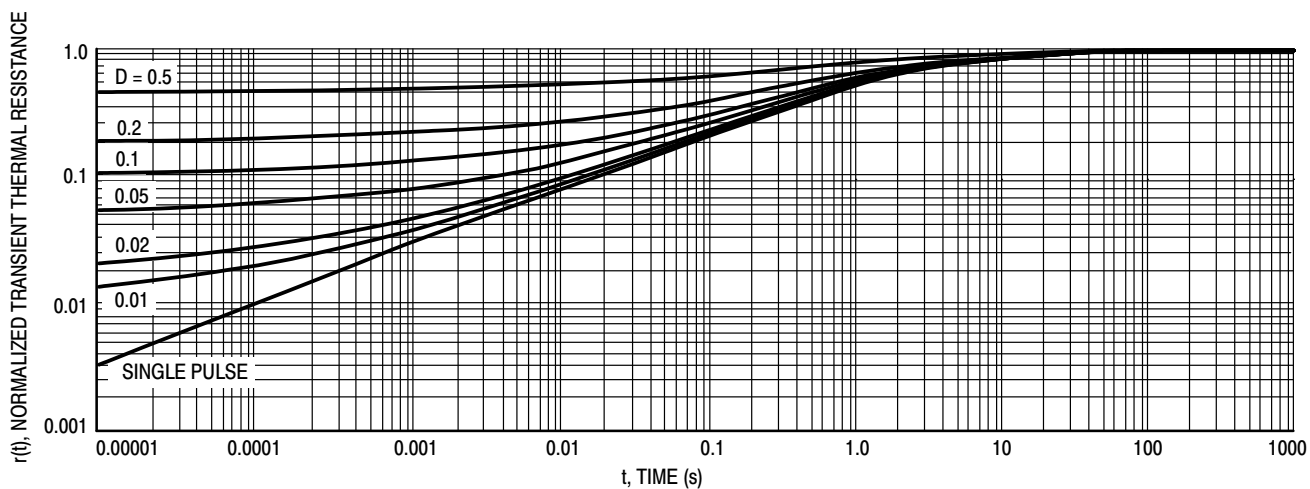
## TYPICAL ELECTRICAL CHARACTERISTICS



**Figure 7. Gate-to-Source Voltage vs. Total Gate Charge**



**Figure 8. Diode Forward Voltage vs. Current**



**Figure 9. Normalized Thermal Response**

## NTA4151P, NTE4151P

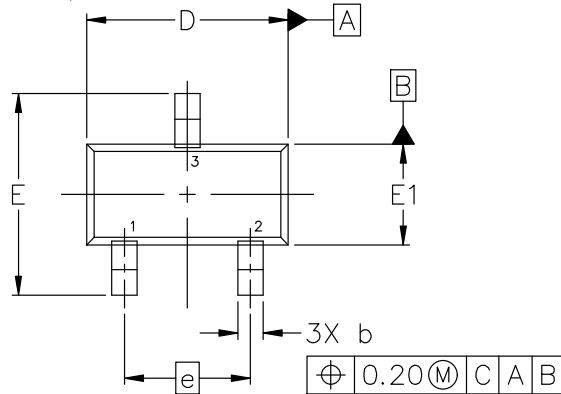
### REVISION HISTORY

Revision	Description of Changes	Date
9	Rebranded the Data Sheet to <b>onsemi</b> format.	10/29/2025

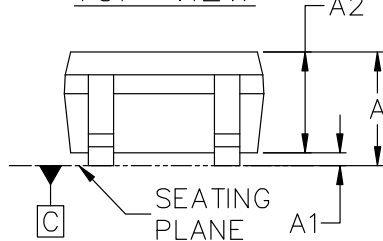
This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

**SC75-3 1.60x0.80x0.80, 1.00P**  
**CASE 463**  
**ISSUE H**

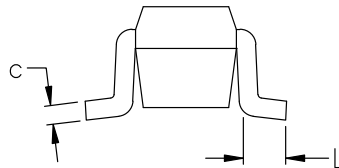
DATE 01 FEB 2024



TOP VIEW

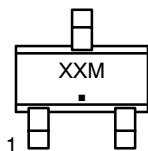


SIDE VIEW



END VIEW

**GENERIC MARKING DIAGRAM\***



XX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

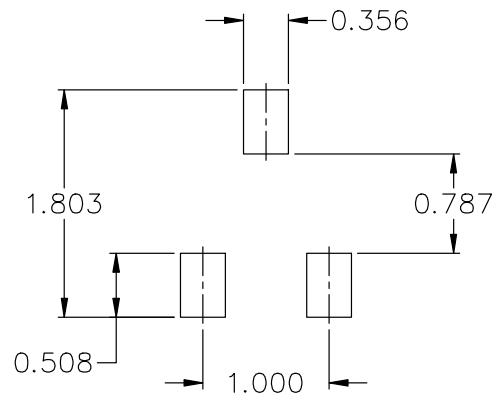
STYLE 2:  
PIN 1. ANODE  
2. N/C  
3. CATHODE

STYLE 3:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 4:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

STYLE 5:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.80	0.90
A1	0.00	0.05	0.10
A2	0.80 REF.		
b	0.15	0.20	0.30
c	0.10	0.15	0.25
D	1.55	1.60	1.65
E	1.50	1.60	1.70
E1	0.70	0.80	0.90
e	1.00 BSC		
L	0.10	0.15	0.20

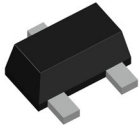


**RECOMMENDED MOUNTING FOOTPRINT\***

\* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

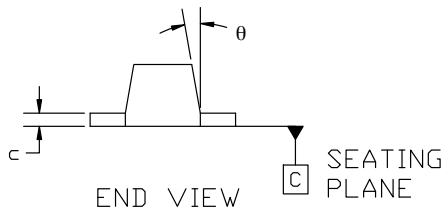
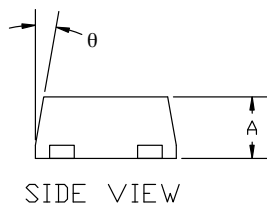
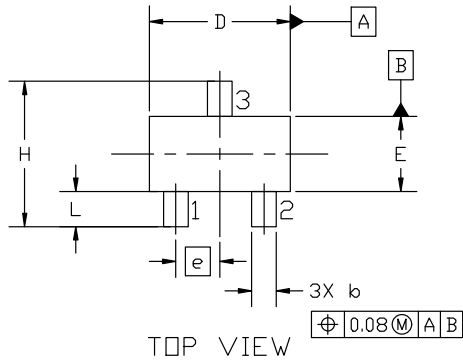
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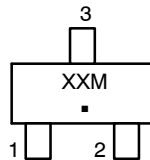


**SC-89 3-LEAD, 1.60x0.85x0.70, 0.50P**  
**CASE 463C**  
**ISSUE D**

DATE 20 FEB 2024



**GENERIC MARKING DIAGRAM\***



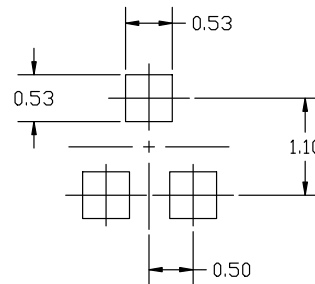
XX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.60	0.70	0.80
b	0.23	0.28	0.33
c	0.10	0.15	0.20
D	1.50	1.60	1.70
E	0.75	0.85	0.95
e	0.50 BSC		
H	1.50	1.60	1.70
L	0.30	0.40	0.50
θ	---	---	10°



**RECOMMENDED MOUNTING FOOTPRINT**

\* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

STYLE 1:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 2:  
PIN 1. ANODE  
2. N/C  
3. CATHODE

STYLE 3:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 4:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

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